

A highly enhanced photoelectrochemical performance of BiVO₄ photoanodes modified with CoPi groups by increasing energy band bending, accelerating hole separation and improving water oxidation kinetics

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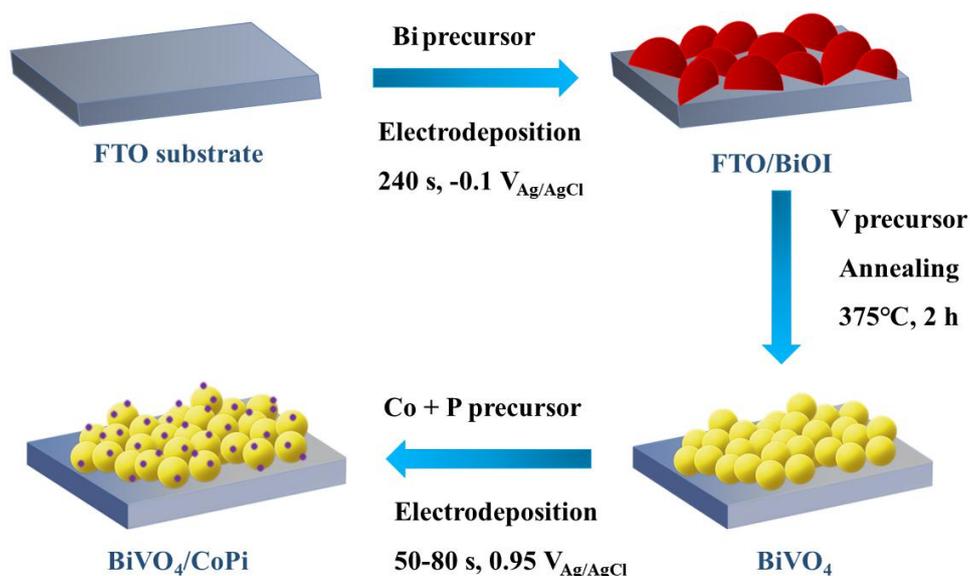


Figure S1 Synthetic process of bare BiVO₄ and BiVO₄/CoPi photoanodes.

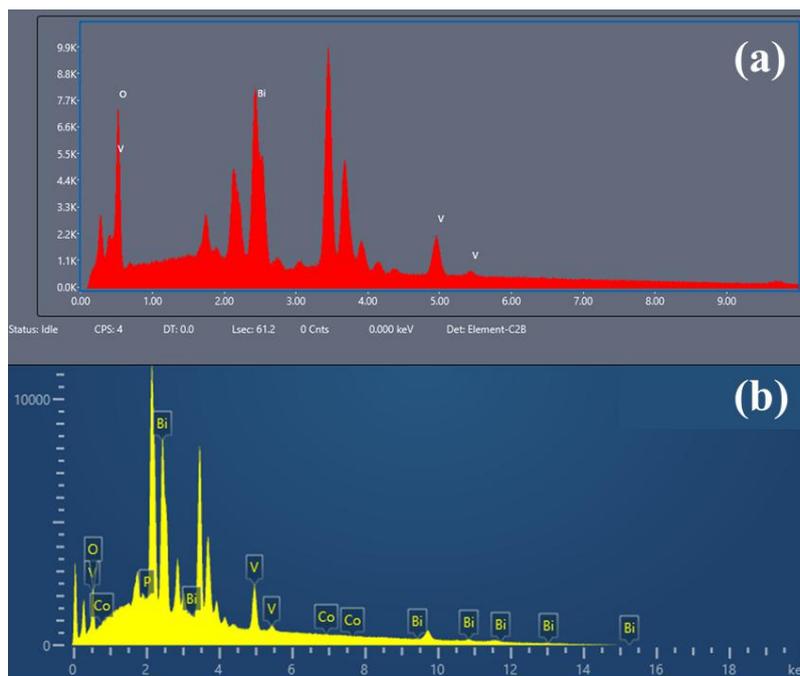


Figure S2 EDX scanning spectra of (a) BiVO_4 and (b) $\text{BiVO}_4/\text{CoPi}$.

Table S1 The content of the corresponding elements in BiVO_4 and $\text{BiVO}_4/\text{CoPi}$ from the EDX scanning spectra.

Element	wt%		at%	
	BiVO_4	$\text{BiVO}_4/\text{CoPi}$	BiVO_4	$\text{BiVO}_4/\text{CoPi}$
Bi	62.86	71.92	16.82	23.94
V	19.44	14.98	21.33	20.46
O	17.70	12.67	61.85	55.10
Co	0	0.43	0	0.50

Table S2 The content of each element in BiVO_4 and $\text{BiVO}_4/\text{CoPi}$ from the XPS spectra of overall survey.

Sample	BiVO_4	$\text{BiVO}_4/\text{CoPi}$
Name	Atomic %	Atomic %
Bi 4f	16.62	13.58
V 2p	25.13	23.23
O 1s	59.25	54.75
Co 2p	0	2.98
P 2p	0	5.45

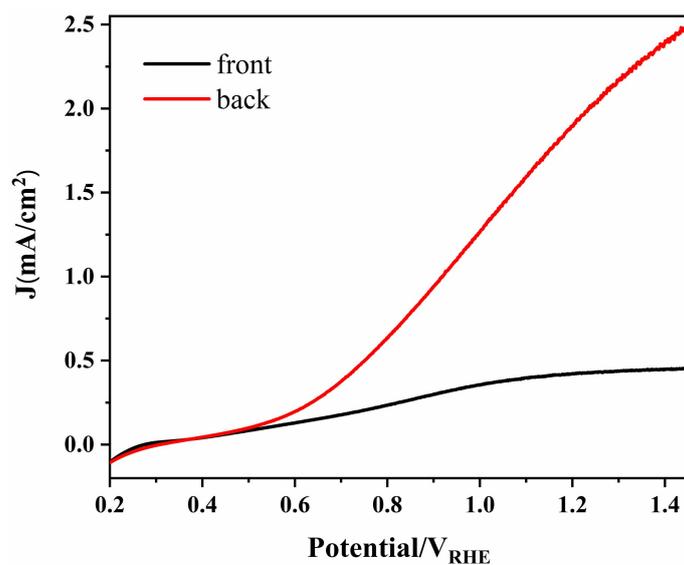


Figure S3 LSV curves of BiVO₄ photoanode front and back irradiation.

Table S3 Comparisons of photoelectrochemical performance of reported previously BiVO₄-based photoanode with our results.

Photoelectrode	Fabrication process	Test condition	Bias	Photocurrent density(mA/cm ²)			Ref.
				bare	Treated	Fold	
BiVO ₄ /CoPi	electrodeposition process	2 M NaBi	1.23 V	1.81	5.87	3.24	This work
Co:BiVO ₄	spin coating	0.5 M Na ₂ SO ₄	1.23 V	0.22	0.46	2.09	[1]
BiVO ₄ /Co(CO ₃) _x	hydrothermal process	1 M NaOH	1.23 V	2.20	5.00	2.27	[2]
OH _y							
WO ₃ /BiVO ₄	sol - gel process	0.1 M KPi	1.23 V	0.53	2.50	4.72	[3]
Li:BiVO ₄	pulsed laser deposition	0.1 M PBS (pH=7)	1.23 V	0.74	0.87	1.18	[4]
Au:BiVO ₄	solution drop casting	0.1 M KOH	1.23 V	0.07	0.24	3.43	[5]
BiVO ₄ /Co(OH)F	solution drop casting	0.5 M KPi	1.23 V	1.45	3.40	2.40	[6]
SnO ₂ @BiVO ₄ /Co-	electrodeposition process	0.1 M PBS	1.23 V	0.40	2.63	6.58	[7]

Pi		(pH=7)					
Mo:BiVO ₄	hydrothermal process	0.1 M Na ₂ SO ₄	1.23 V	1.25	1.70	1.36	[8]
MCo ₂ O ₄ (M=Mn, Zn)/BiVO ₄	spin coating	0.5 M KPi	1.23 V	0.80	2.80	3.5	[9]
Mo,W:BiVO ₄ /PC	solution drop casting	0.1 M Na ₂ SO ₄	1.23 V	0.4	2.50	6.25	[10]
α-Fe ₂ O ₃							
BiVO ₄ /CoSi	PEPD	0.5 M K ₂ B ₄ O ₇	1.23 V	1.7	5.0	2.9	[11]
		(pH=9.5)					
F-BiVO ₄ @NiFe-L	electrodeposition process	0.1 M PBS	1.23 V	0.45	2.67	6.0	[12]
DH		(pH=7)					
CoPi/PANI/ BiVO ₄	PEPD	0.5 M KH ₂ PO ₄	1.23 V	0.98	4.05	4.13	[13]
BiVO ₄ -N/C-CoPO	dipping process	0.5 M PBS	1.23 V	0.61	3.30	5.4	[14]
M							
CoFeOH/Cu ₂ S/ BiVO ₄	SILAR	0.5 M PBS	1.23 V	2.03	3.07	1.51	[15]
BiVO ₄ /WO ₃ NRs	hydrothermal process	0.5 M KPi	1.23 V	0.40	0.64	1.60	[16]
BiVO ₄ /WO ₃ /ITO	pulsed laser deposition	0.5 M Na ₂ SO ₄	1.23 V	0.35	0.86	2.46	[17]
N-BiVO ₄	solution drop casting	0.1 M KPi	1.23 V	1.6	3.3	2.1	[18]
CoP/BiVO ₄	solution drop casting	KBi (pH=9)	1.23 V	2.0	4.1	2.05	[19]
R-BiVO ₄	dipping process	0.2M KPi	1.23 V	2.24	3.18	2.21	[20]
Mo: BiVO ₄ /	spin coating	0.1 M PBS	1.23 V	0.03	1.1	36.7	[21]

CoOOH

BiVO₄/Co-LaFeO electrodeposition process 0.5 M KPi 1.23 V 0.85 3.40 4 [22]

3

CuTCPP/GO/ dipping process 0.5 M PBS 1.23 V 1.25 5.0 4 [23]

BiVO₄ (pH=9)

FeOOH/Au/ electrodeposition process 0.1 M Na₂SO₄ 1.23 V 1.19 4.64 3.74 [24]

BiVO₄

Co-Ci/Mo: BiVO₄ PEPD 0.5 M Na₂SO₄ 1.23 V 0.82 3.95 4.8 [25]

Unless otherwise specified, all photoelectrochemical tests were carried out under simulated 1 sun (AM 1.5 G, 100mW · cm⁻²) illumination and all biases were converted to RHE (V_{RHE}). The fabrication process represents the modification way of bare BiVO₄.

Involved abbreviations: PC, partially covered; PEPD, photoelectrophoretic deposition; PBS, phosphate buffer saline; PANI, polyaniline; SILAR, successive ionic layer adsorption; NRs, nanorods; R-BiVO₄, the photoassisted self-reduction of the BiVO₄; Co-Ci, carbon-based cobalt.

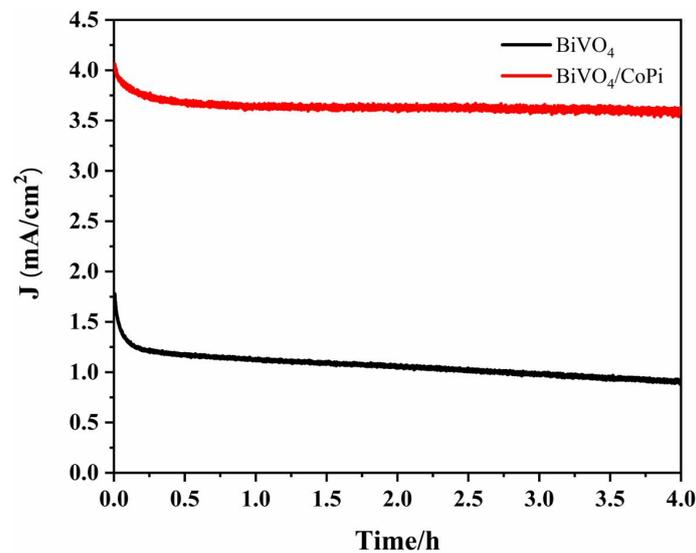


Figure S4 Stability test of 4 h for BiVO₄ and BiVO₄/CoPi films at 1.23 V_{RHE} under AM 1.5G (100 mW cm⁻²) illumination in borate buffer.

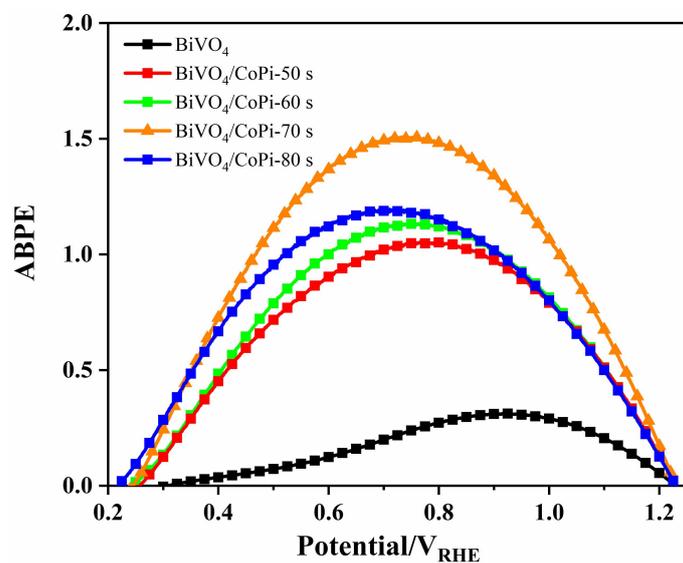


Figure S5 ABPE of BiVO₄ and various deposition times (50-80 s) of BiVO₄/CoPi films with a voltage in the range of 0.2~1.23 V_{RHE}.

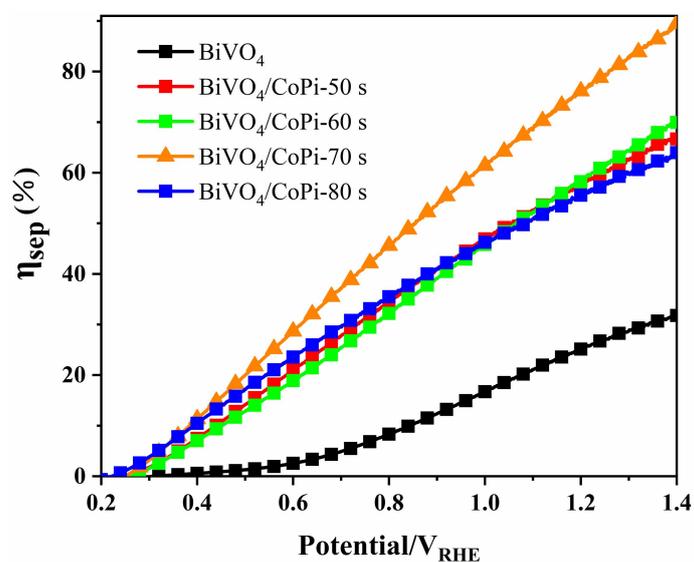


Figure S6 η_{sep} of BiVO₄ and various deposition times (50-80 s) of BiVO₄/CoPi films with a voltage in the range of 0.2~1.4 V_{RHE}.

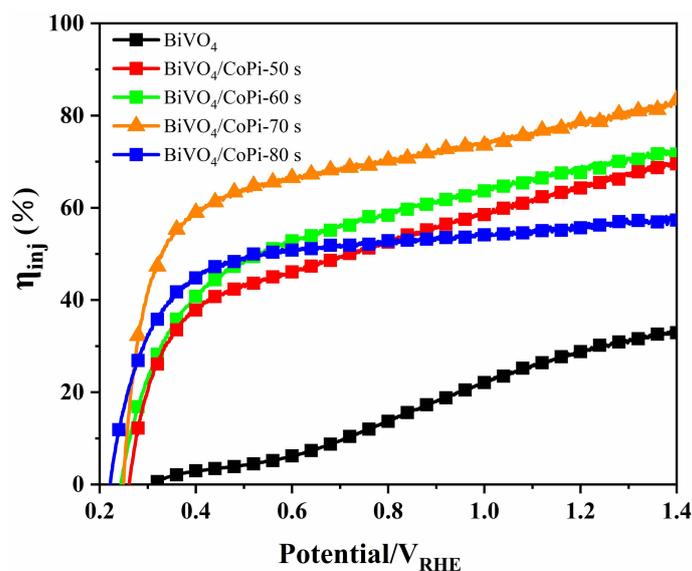


Figure S7 η_{inj} of BiVO_4 and various deposition times (50-80 s) of $\text{BiVO}_4/\text{CoPi}$ films with a voltage in the range of 0.2~1.4 V_{RHE} .

Table S4 Values of the elements in equivalent circuit fitted in the Nyquist plots of Fig. 8a.

sample	R_s/Ω (error/%)	R_{ct}/Ω (error/%)	CPE/F (error/%)
BiVO_4	58.65 (0.78)	194.6 (1.11)	7.49×10^{-5} (5.16)
$\text{BiVO}_4/\text{CoPi}$	51.44 (1.27)	122.0 (3.12)	16.32×10^{-5} (3.76)

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